

Amendments to the Claims:

This listing of the claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1-36 (Canceled)

37 (Presently presented): A semiconductor device comprising:

a plurality of bonding pads, wherein each of the bonding pads has a first metal and a plurality of second metals, each of the plurality of second metals has a linear pattern having a plurality of stripes with a rectangular shape having a long side and a short side in a plan view, is arranged directly under the first metal, and is connected with the first metal; and

a passivation film which covers a side wall and a top surface of the first metal of each of the plurality of bonding pads and has a plurality of openings, each of the plurality of openings exposing a part of the top surface of the first metal of each of the plurality of bonding pads,

wherein in the plan view, the bonding pads are arranged uniformly and in order along the long side direction of the second metal,

wherein a width W at a top and interval D of a bottom of each of the second metals satisfy a relation:

$$W \leq D \leq 2W, \text{ and}$$

in the plan view, an input buffer and an output buffer are formed below each of the plurality of bonding pads, each of the input buffer and the output buffer including a transistor, the input buffer receiving a first signal from the bonding pad and outputting

the first signal to an internal circuit, the output buffer receiving a second signal from the internal circuit and outputting the second signal to the bonding pad.

38 (Canceled)

39 (Previously presented): The semiconductor device according to claim 37, wherein each of the plurality of bonding pads has a third metal arranged under the plurality of second metals and is connected with the plurality of second metals, and wherein the first metal is composed of aluminum and each of the plurality of second metals is composed of tungsten.

40 (Canceled)

41 (Currently amended): The semiconductor device according to claim 37, wherein the first metal and each of the plurality of bonding pads is probed by advancing a probe needle in a direction perpendicular to the long side direction of the second metals.